

Semiconductor Physics, Quantum Electronics & Optoelectronics

Author Index 2000 (Volume 3)

A

- Adadurov A.F.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Khlapova N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Adonkin G.T.** — See Puzikov V.M., Dan'ko A.Ya., Sidel'nikova N.S., Tkachenko V.F., Budnikov A.T., 3(2), 185-190.
- Agueev O.A.** — Simulation of incoherent radiation absorption in 3C-, 6H- and 4H-SiC at rapid thermal processing. — Svetlichny A.M., Soloviev S.I.; 3(3), 379-382.
- Thermoelastic stresses and defect production in semiconductor-insulator structures at isothermic heating Svetlichnyi A.M.; 3(3), 338-342.
- Alexeyev C.N.** — Spin-orbit interaction in a generic vortex field transmitted through an elliptic fiber. — Soskin M.S., Volyar A.V.; 3(4), 500-513.
- Anokhov S.** — Diffraction of optical beams by a half-plane. — Khizhnyak A., Lymarenko R.; 3(1), 94-101.
- Simple waveguide model of arbitrary filled plane-plane cavity; 3(3), 406-409.
- New interpretation of the boundary diffracted wave origin; 3(2), 254-257.
- Arepjev Yu.D.** — See Oleinik V.P., Borimsky Yu.C., 3(4), 558-565.
- Asotsky V.V.** — See Lashkarev G.V., Radchenko M.V., Slyngo E.I., Vodopiyarov V.N., Kaminsky V.M., Beketov G.V., Rengevich E.V., 3(3), 295-299.
- Auleytner J.** — See Żymierska D., Dmitruk N., 3(4), 438-444.
- Ašmontas S.** — Photoresponse of Schottky-barrier detector under strong IR laser excitation. — Seliuta D., Širmulis E.; 3(2), 138-143.
- Babich V.M.** — See Baranskii P.I., Venger E.F., Dotsenko Yu.P., 3(4), 449-452.
- Baranskii P.I.** — The features of magnetoresistance of n-Si doped with phosphorus from the melt and by nuclear transmutation. — Babich V.M., Venger E.F., Dotsenko Yu.P.; 3(4), 449-452.
- Basanets V.V.** — See Boltovets N.S., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
- Baschenko S.M.** — Advanced modification of main types of excimer laser resonators; 3(4), 523-528.
- Multiwave laser source for simultaneous sounding ozone and critically related to ozone chemicals; 3(2), 244-246.
- Science and technology excimer laser complex and examples of its applications. — Blons'kiy I.V.; 3(1), 82-90.
- Batentschuk M.** — See Zorenko Yu., Gorbenko V., Konstantkevych I., Grinev B., Globus M., 3(2), 213-218.
- Bazhenov M.Yu.** — PEPC sensitization with polymethine dyes: Squarylium dyes of indole row as efficient, sensitizers for red region of optical spectrum. — Golod P.I., Grabovskyy V.V., Kurdyukov V.V., Tolmachev A.I., Il'chenko A.Ya., Sokolov N.I., Zahaykevich G., 3(3), 423-425.
- Beketov G.V.** — AFM study of micromorphology and microscopic growth mechanisms of $Hg_{1-x}Cd_xTe$ LPE epitaxial layers. — Rashkovetskiy L.V., Rengevych O.V., Zhovnir G.I.; 3(1), 45-51.
- See Lashkarev G.V., Radchenko M.V., Slyngo E.I., Vodopiyarov V.N., Asotsky V.V., Kaminsky V.M., Rengevich E.V., 3(3), 295-299.
- See Snopok B.A., Kostyukevych K.V., Zinio S.A., Shirshov Y.M., Venger E.F., Verevka S.V., 3(1), 59-68.
- Belyaev A.E.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Konakova R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
- Blons'kiy I.V.** — See Baschenko S.M., 3(1), 82-90.
- Induced polar materials for intense radiation monitoring. — Kosorotov V.F., Shchedrina L.V., Levash L.V.; 3(2), 170-173.
- Boltovets N.S.** — Contacts for silicon IMPATT and pick-off diodes. — Goncharuk N.M., Krivutsa V.A., Chaika V.E., Konakova R.V., Milenin V.V., Soloviev E.A., Tagaev M.B., Voitsikhovskiy D.I.; 3(3), 353-358.
- Microwave diodes with contact metallization systems based on silicides, nitrides and borides of refractory metals. — Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F.; 3(3), 359-370.
- Bonchik A.Yu.** — Melt instabilities on semiconductor surfaces induced by laser radiation. — Dacko B.J., Demchuk V.I., Kiyak S.G., Palyvoda I.P., Shnyr A.F.; 3(3), 311-315.
- Borimsky Yu.C.** — See Oleinik V.P., Arepjev Yu.D., 3(4), 558-565.
- Borisenko A.Yu.** — See Senchishin V.G., Vasilchuk V.L., Lebedev V.N., Adadurov A.F., Khlapova N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Borkovskaya L.V.** — About the nature of diffusion anisotropy in CdS crystals. — Dzhumaev B.R., Khomenkova L.Yu., Korsunskaya N.E., Markevich I.V., Sheinkman M.K.; 3(3), 282-286.
- Borodenko Yu.** — See Zorenko Yu., Lymarenko L., Konstantkevych I., Pashkovskiy M., Moroz Z., Solsky I., Grinev B., Nekrasov V., 3(2), 207-212.
- Borovytsky V.N.** — Residual error after non-uniformity correction; 3(1), 102-105.
- Budnikov A.T.** — See Puzikov V.M., Dan'ko A.Ya., Adonkin G.T., Sidel'nikova N.S., Tkachenko V.F., 3(2), 185-190.
- Burachas S.F.** — Advanced scintillation single crystals based on complex oxides with large atomic number. — Nagornaya L.L., Onishchenko G.M., Piven' L.A., Pirogov E.N., Ryzhikov V.D.; 3(2), 236-239.

C

- Chaika V.E.** — See Boltovets N.S., Goncharuk N.M., Krivutsa V.A., Konakova R.V., Milenin V.V., Soloviev E.A., Tagaev M.B., Voitsikhovskiy D.I., 3(3), 353-358.
- Charkina T.A.** — See Shpilinskaya L.N., Zaslavsky B.G., Kovaleva L.V., Vasetsky S.I., Kudin A.M., Mitichkin A.I., 3(2), 178-180.
- Chernikov V.V.** — See Ryzhikov V.D., Danshin E.A., Starzhinski N.G., Losseva E.A., Litvinov L.A., 3(2), 233-236.

Claeys C. — See Neimash V.B., Puzenko O.O., Kraitchinskii A.M., Kras'ko M.M., Putselyk S., Simoen E., 3(1), 11-14.

D

- Dacko B.J.** — See Bonchik A.Yu., Demchuk V.I., Kiyak S.G., Palyvoda I.P., Shnyr A.F., 3(3), 311-315.
- Dan'ko A.Ya.** — See Puzikov V.M., Adonkin G.T., Sidel'nikova N.S., Tkachenko V.F., Budnikov A.T., 3(2), 185-190.
- Danshin E.A.** — See Ryzhikov V.D., Starzhinski N.G., Losseva E.A., Chernikov V.V., Litvinov L.A., 3(2), 233-236.
- Dariel M.P.** — See Dashevsky Z., Shusterman S., 3(2), 181-184.
- Dashevsky Z.** — Functionally graded PbTe-based compound for thermoelectric applications. — Dariel M.P., Shusterman S.; 3(2), 181-184.
- Datsenko L.I.** — See Klad'ko V.P., Maksimenko Z.V., Lytvyn O.S., Prokopenko I.V., Ā ytkiewicz Z., 3(3), 343-348.
- Davidenko N.A.** — Luminescence and photoconductivity of poly-*n*-epoxypropylcarbazole with intramolecular charge transfer compounds. — Kuvshinsky N.G., Syromiatnikov V.G., 3(1), 39-44.
- Deibuk V.G.** — See Vyklyuk J.I., Rarenko I.M., 3(2), 174-177.
- Demchuk V.I.** — See Bonchik A.Yu., Dacko B.J., Kiyak S.G., Palyvoda I.P., Shnyr A.F., 3(3), 311-315.
- Demidenko A.A.** — Generation of coherent confined acoustic phonons by drifting electrons in quantum wire. — Kochelap V.A.; 3(4), 432-437.
- Piezoelectrically active acoustic waves confined in a quantum well and their amplification by electron drift. — Kochelap V.A., Venger E.F.; 3(4), 427-431.
- Diener J.** — Polarization properties of the luminescence from silicon nanocrystals. — Kovalev D., Polisski G., Koch F.; 3(4), 445-448.
- Dmitruk N.** — See Żymierska D., Auleytner J., 3(4), 438-444.
- Do Y.R.** — See Park C.W., Lee J.-B., Shepeliaviy P., Michailov's'ka K., Indutnyy I., Kudryavtsev A., 3(4), 496-499.
- Dobrotvorskaya M.V.** — See Dubovik M.F., Tolmachev A.V., Grinyov B.V., Grin' L.A., Dolzhenkova E.F., 3(3), 420-422.
- Dolzhenkova E.F.** — See Dubovik M.F., Tolmachev A.V., Grinyov B.V., Grin' L.A., Dobrotvorskaya M.V., 3(3), 420-422.
- Dong Ch.** — See Shcherbak L., Feychuk P., Plevachuk Yu., Sklyarchuk V., 3(4), 456-459.
- Dotsenko Yu.P.** — See Baranskii P.I., Babich V.M., Venger E.F., 3(4), 449-452.
- Dubovik M.F.** — Luminescence and radiation-induced defects in Li₂B₄O₇:Eu single crystals. — Tolmachev A.V., Grinyov B.V., Grin' L.A., Dolzhenkova E.F., Dobrotvorskaya M.V.; 3(3), 420-422.
- See Grinyov B.V., Tolmachev A.V., 3(3), 410-419.
- Dzumaev B.R.** — See Borkovskaya L.V., Khomenkova L.Yu., Korsunskaya N.E., Markevich I.V., Sheinkman M.K., 3(3), 282-286.

E

- Evtukh A.A.** — Field emission of electrons from laser produced silicon tip arrays. — Kaganovich E.B., Litovchenko V.G., Litvin Yu.M., Fedin D.V., Manoilov E.G., Svechnikov S.V.; 3(4), 474-478.

F

- Fedin D.V.** — See Evtukh A.A., Kaganovich E.B., Litovchenko V.G., Litvin Yu.M., Manoilov E.G., Svechnikov S.V., 3(4), 474-478.
- Fedorenko L.** — Laser — induced donor centers in *p*-InSb. — Medvid A.; 3(1), 31-34.
- Fedorov O.A.** — See Zagoruiko Yu.A., Kovalenko N.O., 3(4), 542-544.

- See Zagoruiko Yu.A., Kovalenko N.O., Mateychenko P.V., 3(2), 247-250.
- See Zagoruiko Yu.A., Kovalenko N.O., Rom M.A., Mateychenko P.V., 3(2), 165-169.
- Fedorov A.G.** — Simulation of low angle X-ray diffraction on multilayers subjected to diffusion, 3(4), 554-557.
- Fedorovych R.D.** — See Kovalenko S.A., 3(3), 383-388.
- Fekeshgazi I.V.** — Properties and application of the unequal thickness two-component interference systems. — Pervak V.Yu., Pervak Yu.A.; 3(3), 371-378.
- Feychuk P.** — See Shcherbak L., Plevachuk Yu., Dong Ch., Sklyarchuk V., 3(4), 456-459.
- Fodchoock I.M.** — See Gritsook B.N., Nichiy S.V., Paranchich Y.S., Politanskiy R.L., 3(4), 460-462.
- Freik D.M.** — Thermoelectric properties of solid solutions based on tin telluride. — Galushchak M.O., Ivanishin I.M., Shperun V.M., Zapukhlyak R.I., Pyts M.V.; 3(3), 287-290.

G

- Gal'chinetskii L.P.** — See Volkov V.G., Gavrilyuk V.P., Grinyov B.V., Katrunov K.A., Ryzhikov V.D., 3(2), 191-194.
- Galushchak M.O.** — See Freik D.M., Ivanishin I.M., Shperun V.M., Zapukhlyak R.I., Pyts M.V., 3(3), 287-290.
- Gavrilyuk V.P.** — See Volkov V.G., Gal'chinetskii L.P., Grinyov B.V., Katrunov K.A., Ryzhikov V.D., 3(2), 191-194.
- Globus M.** — See Zorenko Yu., Gorbenko V., Konstankevych I., Grinev B., Batentschuk M., 3(2), 213-218.
- Gnatyuk V.A.** — Modification of photoelectric and electrical properties of III-V semiconductors by pulsed laser irradiation. — Gorodnychenko O.S., Mozol P.O., Vlasenko O.I.; 3(1), 26-30.
- Golod P.I.** — See Bazhenov M.Yu., Grabovskyy V.V., Kurdyukov V.V., Tolmachev A.I., Il'chenko A.Ya., Sokolov N.I., Zahaykevich G., 3(3), 423-425.
- Gomeniuk Y.V.** — See V.S. Lysenko, I.P. Tyagulski, I.N. Osiyuk, 3(3), 330-337.
- Goncharenko A.V.** — Dispersion of natural modes in a many-layer planar system. — Snopok B.A., Shirshov Yu.M., Venger E.F., Zavadskii S.N.; 3(3), 389-393.
- Goncharuk N.M.** — See Boltovets N.S., Krivutsa V.A., Chaika V.E., Konakova R.V., Milenin V.V., Soloviev E.A., Tagaev M.B., Voitsikhovskiy D.I., 3(3), 353-358.
- Gorban' A.P.** — See Sachenko A.V., Kostilyov V.P. 3(1), 5-10.
- Effect of excitons on photoconversion efficiency in the $p^+ - n - n^+ -$ and $n^+ - p - p^+$ -structures based on single-crystalline silicon. — Sachenko A.V., Kostilyov V.P., Prima N.A.; 3(3), 322-329.
- Gorbenko V.** — See Zorenko Yu., Konstankevych I., Grinev B., Globus M., Batentschuk M., 3(2), 213-218.
- Gorbulov V.V.** — See Virt I.S., 3(1), 35-38.
- Gorley P.M.** — See Voznyy M.V., Schenderovskyy V.A., 3(3), 271-274.
- Gorodnychenko O.S.** — See Gnatyuk V.A., Mozol P.O., Vlasenko O.I.; 3(1), 26-30.
- Grabovskyy V.V.** — See Bazhenov M.Yu., Golod P.I., Kurdyukov V.V., Tolmachev A.I., Il'chenko A.Ya., Sokolov N.I., Zahaykevich G., 3(3), 423-425.
- Griban V.M.** — Some features of two-photon absorption in static electric field. — Melnichuk O.V., Ovander L.M., Venger E.F.; 3 (2), 144-149.
- Grigorchuk N.I.** — Polarization operator of phonons in quadratic approximation; 3(3), 316-321.
- Grin' L.A.** — See Dubovik M.F., Tolmachev A.V., Grinyov B.V., Dolzhenkova E.F., Dobrotvorskaya M.V., 3(3), 420-422.
- Grinev B.** — See Zorenko Yu., Gorbenko V., Konstankevych I., Globus M., Batentschuk M., 3(2), 213-218.
- See Zorenko Yu., Limarenko L., Konstankevych I., Pashkovsky M., Moroz Z., Solsky I., Nekrasov V., Borodenko Yu., 3(2), 207-212.

- Grinyov B.V.** — Borate single crystals for polyfunctional applications: — See Dubovik M.F., Tolmachev A.V., Grin' L.A., Dolzhenkova E.F., Dobrotvorskaya M.V., 3(3), 420-422.
— See Volkov V.G., Gavrilyuk V.P., Gal'chinetskii L.P., Katrunov K.A., Ryzhikov V.D., 3(2), 191-194.
- Gritsook B.N.** — Growing Cd_{0.25}Hg_{0.75}Se layers by laser evaporation in static vacuum. — Fodchoock I.M., Nichiy S.V., Paranchich Y.S., Politanskiy R.L.; 3(4), 460-462.
- Gumenjuk A.F.** — Oscillator regularity of the trap activation energies in NaCl crystals. — Kutovy S.Yu., Kurilova V.A.; 3(4), 463-468.

H

- Holovey V.M.** — See Hunda B.M., Puga P.P., Solomon A.M., 3(2), 227-232.
- Hunda B.M.** — Thermostimulated luminescence and the temperature dependence of X-ray luminescence of the Li₂B₄O₇ single crystals. — Puga P.P., Solomon A.M., Holovey V.M.; 3(2), 227-232.

I

- Ignatovych M.** — Radioluminescent, thermoluminescent and dosimetric properties of X-ray phosphors. — Kelemen A., Otvash N., Peto A., Ogenko V.; 3(2), 240-243.
- Il'chenko A.Ya.** — See Bazhenov M.Yu., Golod P.I., Grabovskyy V.V., Kurdyukov V.V., Tolmachev A.I., Sokolov N.I., Zakhaykevich G., 3(3), 423-425.
- Ilichuk G.A.** — Photopleochroism of surface-barrier structures based on semiinsulating cadmium telluride; 3(3), 349-351.
- Indutnyy I.Z.** — See Park C.W., Lee J.-B., Do Y.R., Shepeliavyy P., Michailovs'ka K., Kudryavtsev A., 3(4), 496-499.
— See Min'ko V.I., Romanenko P.F., Kudryavtsev A.A., 3(2), 251-253.
- Ishchenko S.** — See Vorona I., Okulov S., Petrenko T.T., 3(2), 219-222.
- Ivanishin I.M.** — See Freik D.M., Galushchak M.O., Shperun V.M., Zapukhlyak R.I., Pyts M.V., 3(3), 287-290.
- Ivanov V.N.** — See Boltovets N.S., Basanets V.V., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.

K

- Kaganovich E.B.** — See Evtukh A.A., Litovchenko V.G., Litvin Yu.M., Fedin D.V., Manoilov E.G., Svechnikov S.V., 3(4), 474-478.
- Kaminsky V.M.** — See Lashkarev G.V., Radchenko M.V., Slynko E.I., Vodopyanov V.N., Asotsky V.V., Beketov G.V., Rengevich E.V., 3(3), 295-299.
- Karachevtseva L.A.** — Development and optical characteristics of the macroporous silicon structures. — Lytyvnenko O.A., Stronska O.J.; 3(1), 22-25.
- Katrunov K.A.** — See Volkov V.G., Gavrilyuk V.P., Gal'chinetskii L.P., Grinyov B.V., Ryzhikov V.D., 3(2), 191-194.
- Kelemen A.** — See Ignatovych M., Otvash N., Peto A., Ogenko V., 3(2), 240-243.
- Khizhnyak A.** — See Anokhov S., Lymarenko R., 3(1), 94-101.
- Khlapova N.P.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Kholevchuk V.V.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova

- R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Mitin V.F., 3(3), 359-370.
- Khomenkova L.Yu.** — See Borkovskaya L.V., Dzhumaev B.R., Korsunskaya N.E., Markevich I.V., Sheinkman M.K., 3(3), 282-286.
- Kislovskii E.N.** — See Prokopenko I.V., Olikhovskii S.I., Tkach V.M., Lytvyn P.M., Vladimirova T.P., 3(3), 275-281.
- Kissel H.** — See Masselink W.T., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Lisitsa M.P., Lavoric S.R., Zhuchenko Z.Ya., 3(2), 121-125.
— See Masselink W.T., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Rud'ko G.Yu., Valakh M.Ya., Malyarchuk V., Zhuchenko Z.Ya., 3(2), 126-137.
- Kiv A.E.** — Microstructure of the relaxed (001) Si surface. — Soloviev V.N., Maximova T.I.; 3(2), 157-160.
- Kiyak S.G.** — See Bonchik A.Yu., Dacko B.J., Demchuk V.I., Palyvoda I.P., Shnyr A.F., 3(3), 311-315.
- Klad'ko V.P.** — Structural and composition irregularities in GaAs:Si/GaAs films grown by liquid-phase epitaxy. — Datsenko L.I., Maksimenko Z.V., Lytvyn O.S., Prokopenko I.V., Žytkevich Z.; 3(3), 343-348.
- Kluban N.A.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Koba V.S.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P., Titskaja V.D., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Koch F.** — See Diener J., Kovalev D., Polisski G., 3(4), 445-448.
- Kochelap V.A.** — See Demidenko A.A., 3(4), 432-437.
— See Demidenko A.A., Venger E.F., 3(4), 427-431.
- Kolesnyk P.V.** — See Shaykevich I.A., 3(1), 77-81.
- Kolomoets V.V.** — See Venger Ye.F., Machulin V.F., 3(3), 291-294.
- Kolybayeva M.I.** — See Salo V.I., Tkachenko V.F., Pritula I.M., 3(2), 203-206.
- Konakova R.V.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
— See Boltovets N.S., Goncharuk N.M., Krivutsa V.A., Chaika V.E., Milenin V.V., Soloviev E.A., Tagaev M.B., Voitsikhovskiy D.I., 3(3), 353-358.
- Kondrachuk A.V.** — See Shwarts Yu.M., Shwarts M.M., Shpinar L.I., 3(3), 400-405.
- Kondratenko S.V.** — See Vakulenko O.V., 3(4), 453-455.
- Konstankevych I.** — See Zorenko Yu., Gorbenko V., Grinev B., Globus M., Batentschuk M., 3(2), 213-218.
— See Zorenko Yu., Limarenko L., Pashkovskiy M., Moroz Z., Solsky I., Grinev B., Nekrasov V., Borodenko Yu., 3(2), 207-212.
- Korsunskaya N.E.** — See Borkovskaya L.V., Dzhumaev B.R., Khomenkova L.Yu., Markevich I.V., Sheinkman M.K., 3(3), 282-286.
- Kosorotov V.F.** — See Blonsky I.V., Shchedrina L.V., Levash L.V., 3(2), 170-173.
- Kostilyov V.P.** — See Gorban' A.P., Sachenko A.V., Prima N.A., 3(3), 322-329.
— See Sachenko A.V., Gorban A.P. 3(1), 5-10.
- Kostyukevych K.V.** — See Snopok B.A., Beketov G.V., Zinio S.A., Shirshov Y.M., Venger E.F., Verevka S.V., 3(1), 59-68.
- Kovalchuk V.V.** — See Pokutnyi S.I., 3(1), 69-76.
- Kovalenko N.O.** — See Zagoruiko Yu.A., Fedorenko O.A., 3(4), 542-544.
— See Zagoruiko Yu.A., Fedorenko O.A., Mateychenko P.V., 3(2), 247-250.

- See Zagoruiko Yu.A., Fedorenko O.A., Rom M.A., Mateychenko P.V., 3(2), 165-169.
- Kovalenko S.A.** - Dimensional effects in thin gold films; 3(4), 514-519.
- Optical properties of thin gold films. — Fedorovych R.D.; 3(3), 383-388.
- Kovalev D.** — See Diener J., Polisski G., Koch F., 3(4), 445-448.
- Kovaleva L.V.** — See Shpilinskaya L.N., Zaslavsky B.G., Vasetsky S.I., Kudin A.M., Mitichkin A.I., Charkina T.A., 3(2), 178-180.
- Kraitchinskii A.M.** — See Neimash V.B., Puzenko O.O., Kras'ko M.M., Putselyk S., Claeys C. Simoen E., 3(1), 11-14.
- Kras'ko M.M.** — See Neimash V.B., Puzenko O.O., Kraitchinskii A.M., Putselyk S., Claeys C. Simoen E., 3(1), 11-14.
- Kravets V.G.** — Characterization and optical properties of organic dye films as recording media. — Vinnichenko K.L., Prygun O.V.; 3(4), 520-522.
- Krivutsa V.A.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Tsvir A.V., Belyaev A.E., Konakova R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
- Krivutsa V.A.** — See Boltovets N.S., Goncharuk N.M., Chaika V.E., Konakova R.V., Milenin V.V., Soloviev E.A., Tagaev M.B., Voitsikhovskiy D.I., 3(3), 353-358.
- Kruglenko I.V.** — Digital aroma technology for chemical sensing: temporal chemical images of complex mixtures. — Snopok B.A., Shirshov Y.M., Venger E.F.; 3(4), 529-541.
- Kryuchenko Yu.V.** — See Sachenko A.V., 3 (2), 149-156.
- Krüger D.** — See Romanjuk B., Melnik V., Popov V., Olikh Ya., Soroka V., Oberemok O., 3(1), 15-18.
- Kudin A.M.** — See Shpilinskaya L.N., Zaslavsky B.G., Kovaleva L.V., Vasetsky S.I., Mitichkin A.I., Charkina T.A., 3(2), 178-180.
- Kudin A.P.** — Radiation-induced changes in infra-red spectrum of black zinc diphosphide monocrystals; 3(2), 161-164.
- Kudryavtsev A.A.** — Heat flux effect on photoenhanced and dark silver motion in a thin As₂S₃ layer. — Michailovskaya E.V.; 3(4), 469-473.
- See Min'ko V.I., Indutnyy I.Z., Romanenko P.F., 3(2), 251-253.
- See Park C.W., Lee J.-B., Do Y.R., Shepeliavii P., Michailovs'ka K., Indutnyy I., 3(4), 496-499.
- Kurdyukov V.V.** — See Bazhenov M.Yu., Golod P.I., Grabovskyy V.V., Tolmachev A.I., Il'chenko A.Ya., Sokolov N.I., Zahaykevich G., 3(3), 423-425.
- Kurilova V.A.** — See Gumenjuk A.F., Kutovyi S.Yu., 3(4), 463-468.
- Kutovyi S.Yu.** — See Gumenjuk A.F., Kurilova V.A., 3(4), 463-468.
- Kuvshinsky N.G.** — See Davidenko N.A., Syromiatnikov V.G., 3(1), 39-44.

L

- Lashkarev G.V.** — Hot wall growth and properties of lead telluride films doped by germanium and gallium. — Radchenko M.V., Slynko E.I., Vodopyanov V.N., Asotsky V.V., Kaminsky V.M., Beketov G.V., Rengevich E.V.; 3(3), 295-299.
- Lavoric S.R.** — See Masselink W.T., Kissel H., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Lisitsa M.P., Zhuchenko Z.Ya., 3(2), 121-125.
- Lebedev V.N.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Adadurov A.F., Khlapova N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Lee J.-B.** — See Park C.W., Do Y.R., Shepeliavii P., Michailovs'ka K., Indutnyy I., Kudryavtsev A., 3(4), 496-499.
- Leman V.E.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P.,

- Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Lepikh Ya.I.** — Physical mechanism for temperature oscillations of ferroelectric ceramics conduction; 3(3), 308-310.
- Strain effect in surface acoustic wave elements with a piezoelectric acoustic line and sensors based on this effect; 3(1), 91-93.
- Levash L.V.** — See Blonsky I.V., Kosorotov V.F., Shchedrina L.V., 3(2), 170-173.
- Limarenko L.** — See Zorenko Yu., Konstankevych I., Pashkovsky M., Moroz Z., Solsky I., Grinev B., Nekrasov V., Borodenko Yu., 3(2), 207-212.
- Lisitsa M.P.** — See Masselink W.T., Kissel H., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Lavoric S.R., Zhuchenko Z.Ya., 3(2), 121-125.
- Litovchenko V.G.** — See Evtukh A.A., Kaganovich E.B., Litvin Yu.M., Fedin D.V., Manoilov E.G., Svechnikov S.V., 3(4), 474-478.
- Litvin Yu.M.** — See Evtukh A.A., Kaganovich E.B., Litovchenko V.G., Fedin D.V., Manoilov E.G., Svechnikov S.V., 3(4), 474-478.
- Litvinov L.A.** — See Ryzhikov V.D., Danshin E.A., Starzhinski N.G., Losseva E.A., Chernikov V.V., 3(2), 233-236.
- Losseva E.A.** — See Ryzhikov V.D., Danshin E.A., Starzhinski N.G., Chernikov V.V., Litvinov L.A., 3(2), 233-236.
- Lyapin V.G.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova R.V., Milenin V.V., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
- Lymarenko R.** — See Anokhov S., Khizhnyak A., 3(1), 94-101.
- Lysenko V.S.** — Effect of the charge state of traps on the transport current in the SiC/Si heterostructure. — Tyagulski I.P., Gomeniuk Y.V., Osiyuk I.N.; 3(3), 330-337.
- Lytvyn O.S.** — See Klad'ko V.P., Datsenko L.I., Maksimenko Z.V., Prokopenko I.V., Ytkiewicz Z., 3(3), 343-348.
- Lytvyn P.M.** — See Prokopenko I.V., Kislovskii E.N., Olikhovskii S.I., Tkach V.M., Vladimirova T.P., 3(3), 275-281.
- Lytvnenko O.A.** — See Karachevtseva L.A., Stronska O.J. 3(1), 22-25.

M

- Machulin V.F.** — See Venger Ye.F., Kolomoets V.V., 3(3), 291-294.
- Makarov I.M.** — See Pokropivny V.V., Pokropivny A.V., 3(4), 550-553.
- Maksimenko Z.V.** — See Klad'ko V.P., Datsenko L.I., Lytvyn O.S., Prokopenko I.V., Ytkiewicz Z., 3(3), 343-348.
- Malyarchuk V.** — See Masselink W.T., Kissel H., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Rud'ko G.Yu., Valakh M.Ya., Zhuchenko Z.Ya., 3(2), 126-137.
- Manoilov E.G.** — See Evtukh A.A., Kaganovich E.B., Litovchenko V.G., Litvin Yu.M., Fedin D.V., Svechnikov S.V., 3(4), 474-478.
- Markevich I.V.** — See Borkovskaya L.V., Dzhumaev B.R., Khomenkova L.Yu., Korsunskaya N.E., Sheinkman M.K., 3(3), 282-286.
- Masselink W.T.** — InAs quantum dots embedded into anti-modulation-doped GaAs superlattice structures. — Kissel H., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Lisitsa M.P., Lavoric S.R., Zhuchenko Z.Ya.; 3(2), 121-125.
- Pseudomorphic modulation-doped AlGaAs/InGaAs/GaAs heterostructures with strong manifestation of many-body effects. — Kissel H., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Rud'ko G.Yu., Valakh M.Ya., Malyarchuk V., Zhuchenko Z.Ya.; 3(2), 126-137.
- Mateychenko P.V.** — See Zagoruiko Yu.A., Fedorenko O.A., Kovalenko N.O., Rom M.A., 3(2), 165-169.
- See Zagoruiko Yu.A., Fedorenko O.A., Kovalenko N.O., 3(2), 247-250.

- Maximova T.I.** — See Kiv A.E., Soloviev V.N., 3(2), 157-160.
- Mazur Yu.I.** — See Masselink W.T., Kissel H., Mueller U., Walther C., Tarasov G.G., Lisitsa M.P., LAVORIC S.R., Zhuchenko Z.Ya., 3(2), 121-125.
— See Masselink W.T., Kissel H., Mueller U., Walther C., Tarasov G.G., Rud'ko G.Yu., Valakh M.Ya., Malyarchuk V., Zhuchenko Z.Ya., 3(2), 126-137.
- Medvid A.** — See Fedorenko L., 3(1), 31-34.
- Melnichuk O.V.** — See Griban V.M., Ovander L.M., Venger E.F., 3 (2), 144-149.
- Melnik V.** — See Romanjuk B., Krüger D., Popov V., Olikh Ya., Soroka V., Oberemok O., 3(1), 15-18.
- Michailovs'ka K.** — See Park C.W., Lee J.-B., Do Y.R., Shepeliavyy P., Indutnyy I., Kudryavtsev A., 3(4), 496-499.
- Michailovskaya E.V.** — See Kudryavtsev A.A., 3(4), 469-473.
- Milenin V.V.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova R.V., Lyapin V.G., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
— See Boltovets N.S., Goncharuk N.M., Krivutsa V.A., Chaika V.E., Konakova R.V., Soloviev E.A., Tagaev M.B., Voitsikhovskiy D.I., 3(3), 353-358.
- Min'ko V.I.** — Recording of rainbow holograms using As_2Se_3 amorphous layers. — Indutnyy I.Z., Romanenko P.F., Kudryavtsev A.A.; 3(2), 251-253.
- Miroshnichenko L.A.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Mitichkin A.I.** — See Shpilinskaya L.N., Zaslavsky B.G., Kovaleva L.V., Vasetsky S.I., Kudin A.M., Charkina T.A., 3(2), 178-180.
- Mitin V.F.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Kholevchuk V.V., Voitsikhovskiy D.I., 3(3), 359-370.
- Mitsaj L.I.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., 3(2), 223-226.
- Moroz Z.** — See Zorenko Yu., Limarenko L., Konstankevych I., Pashkovsky M., Solsky I., Grinev B., Nekrasov V., Borodenko Yu., 3(2), 207-212.
- Movchan S.** — See Tetyorkin V., 3(3), 300-303.
- Mozol P.O.** — See Gnatyuk V.A., Gorodnychenko O.S., Vlasenko O.I.; 3(1), 26-30.
- Mueller U.** — See Masselink W.T., Kissel H., Walther C., Mazur Yu.I., Tarasov G.G., Lisitsa M.P., LAVORIC S.R., Zhuchenko Z.Ya., 3(2), 121-125.
— See Masselink W.T., Kissel H., Walther C., Mazur Yu.I., Tarasov G.G., Rud'ko G.Yu., Valakh M.Ya., Malyarchuk V., Zhuchenko Z.Ya., 3(2), 126-137.

N

- Nagornaya L.L.** — See Burachas S.F., Onishchenko G.M., Piven' L.A., Pirogov E.N., Ryzhikov V.D., 3(2), 236-239.
- Neimash V.B.** — Microfluctuations of oxygen impurity concentration as a reason of accelerated oxygen diffusion in silicon. — Puzenko O.O., Kraitichinskii A.M., Kras'ko M.M., Putselyk S., Claeys C., Simoen E.; 3(1), 11-14.
- Nekrasov V.** — See Zorenko Yu., Limarenko L., Konstankevych I., Pashkovsky M., Moroz Z., Solsky I., Grinev B., Borodenko Yu., 3(2), 207-212.
- Nichiy S.V.** — See Gritsook B.N., Fodchoock I.M., Paranchich Y.S., Politanskiy R.L., 3(4), 460-462.

O

- Oberemok O.** — See Romanjuk B., Krüger D., Melnik V., Popov V., Olikh Ya., Soroka V., 3(1), 15-18.
- Ogenko V.** — See Ignatovych M., Kelemen A., Otvas N., Peto A., 3(2), 240-243.
- Okulov S.** — See Vorona I., Ishchenko S., Petrenko T.T., 3(2), 219-222.
- Oleinik V.P.** — New ideas in electrodynamics: physical properties of time. — Borimsky Yu.C., Arepjev Yu.D., 3(4), 558-565.
- Olikh Y.M.** — Acoustodynamic transformation of the defect structure in Hg 1-x Cd x Te alloys. — Savkina R.K., Vlasenko O.I., 3(3), 304-307.
- Olikh Ya.** — See Romanjuk B., Krüger D., Melnik V., Popov V., Soroka V., Oberemok O., 3(1), 15-18.
- Olikhovskii S.I.** — See Prokopenko I.V., Kislovskii E.N., Tkach V.M., Lytvyn P.M., Vladimirova T.P., 3(3), 275-281.
- Onishchenko G.M.** — See Burachas S.F., Nagornaya L.L., Piven' L.A., Pirogov E.N., Ryzhikov V.D., 3(2), 236-239.
- Osadchenko V.N.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A. — See Leman V.E., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Osiyuk I.N.** — See V.S. Lysenko, I.P. Tyagulski, Y.V. Gomeniuk, 3(3), 330-337.
- Otvas N.** — See Ignatovych M., Kelemen A., Peto A., Ogenko V., 3(2), 240-243.
- Ovander L.M.** — See Griban V.M., Melnichuk O.V., Venger E.F., 3(2), 144-149.

P

- Palyoda I.P.** — See Bonchik A.Yu., Dacko B.J., Demchuk V.I., Kiyak S.G., Shnyr A.F., 3(3), 311-315.
- Paranchich Y.S.** — See Gritsook B.N., Fodchoock I.M., Nichiy S.V., Politanskiy R.L., 3(4), 460-462.
- Park C.W.** — Metal-dielectric black matrix for display devices. — Lee J.-B., Do Y.R., Shepeliavyy P., Michailovs'ka K., Indutnyy I., Kudryavtsev A.; 3(4), 496-499.
- Pashkovsky M.** — See Zorenko Yu., Limarenko L., Konstankevych I., Moroz Z., Solsky I., Grinev B., Nekrasov V., Borodenko Yu., 3(2), 207-212.
- Pelipyagina L.E.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P., Titskaja V.D., Koba V.S., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Pervak V.Yu.** — See Fekeshgazi I.V., Pervak Yu.A., 3(3), 371-378.
- Pervak Yu.A.** — See Fekeshgazi I.V., Pervak V.Yu., 3(3), 371-378.
- Peto A.** — See Ignatovych M., Kelemen A., Otvas N., Ogenko V., 3(2), 240-243.
- Petrenko T.T.** — See Vorona I., Ishchenko S., Okulov S., 3(2), 219-222.
- Pirogov E.N.** — See Burachas S.F., Nagornaya L.L., Onishchenko G.M., Piven' L.A., Ryzhikov V.D., 3(2), 236-239.
- Piven' L.A.** — See Burachas S.F., Nagornaya L.L., Onishchenko G.M., Pirogov E.N., Ryzhikov V.D., 3(2), 236-239.
- Plevachuk Yu.** — See Shcherbak L., Feychuk P., Dong Ch., Sklyarchuk V., 3(4), 456-459.
- Pokropivny A.V.** — See Pokropivny V.V., Makarov I.M., 3(4), 550-553.
— See Sheichenko D.M., Pokropivny V.V., 3(4), 545-549.
- Pokropivny V.V.** — Lattice of superconducting multilayer nanotubes as ideal high-temperature superconductor. — Makarov I.M., Pokropivny A.V.; 3(4), 550-553.

- Pokropivny V.V.** — See Sheichenko D.M., Pokropivny A.V., 3(4), 545-549.
- Pokutnyi S.I.** — Theoretical investigation of light absorption and scattering by nanoparticles. — Kovalchuk V.V.; 3(1), 69-76.
- Polisski G.** — See Diener J., Kovalev D., Koch F., 3(4), 445-448.
- Politanskiy R.L.** — See Gritsook B.N., Fodchoock I.M., Nichiy S.V., Paranchich Y.S., 3(4), 460-462.
- Popov V.** — See Romanjuk B., Krüger D., Melnik V., Olikh Ya., Soroka V., Oberemok O., 3(1), 15-18.
- Popov V.G.** — Solar cells based on multicrystalline silicon; 3(4), 479-488.
- Prima N.A.** — See Gorban' A.P., Sachenko A.V., Kostilyov V.P., 3(3), 322-329.
- Pritula I.M.** — See Salo V.I., Tkachenko V.F., Kolybayeva M.I., 3(2), 203-206.
- production and properties. — Dubovik M.F., Tolmachev A.V.; 3(3), 410-419.
- Prokopenko I.V.** — Comprehensive investigation of defects in highly perfect silicon single crystals. — Kislovskii E.N., Olikhovskii S.I., Tkach V.M., Lytvyn P.M., Vladimirova T.P.; 3(3), 275-281.
- See Klad'ko V.P., Datsenko L.I., Maksimenko Z.V., Lytvyn O.S., Ī ytkiewicz Z., 3(3), 343-348.
- Prygun O.V.** — See Kravets V.G., Vinnichenko K.L., 3(4), 520-522.
- Puga P.P.** — See Hunda B.M., Solomon A.M., Holovey V.M., 3(2), 227-232.
- Putselyk S.** — See Neimash V.B., Puzenko O.O., Kraitchinskii A.M., Kras'ko M.M., Claeyns C. Simoen E., 3(1), 11-14.
- Puzenko O.O.** — See Neimash V.B., Kraitchinskii A.M., Kras'ko M.M., Putselyk S., Claeyns C. Simoen E., 3(1), 11-14.
- Puzikov V.M.** — Optical properties and fine faulty structure of sapphire crystals grown in low pressure CO gas atmosphere. — Dan'ko A.Ya., Adonkin G.T., Sidel'nikova N.S., Tkachenko V.F., Budnikov A.T.; 3(2), 185-190.
- Pyts M.V.** — See Freik D.M., Galushchak M.O., Ivanishin I.M., Shperun V.M., Zapukhlyak R.I., 3(3), 287-290.

R

- Radchenko M.V.** — See Lashkarev G.V., Slynko E.I., Vodopyanov V.N., Asotsky V.V., Kaminsky V.M., Beketov G.V., Rengevich E.V., 3(3), 295-299.
- Rarenko I.M.** — See Vykylyuk J.I., Deibuk V.G., 3(2), 174-177.
- Rashkovetskiy L.V.** — See Beketov G.V., Rengevych O.V., Zhovnir G.I., 3(1), 45-51.
- Rengevich E.V.** — See Lashkarev G.V., Radchenko M.V., Slynko E.I., Vodopyanov V.N., Asotsky V.V., Kaminsky V.M., Beketov G.V., 3(3), 295-299.
- Rengevych O.V.** — See Beketov G.V., Rashkovetskiy L.V., Zhovnir G.I., 3(1), 45-51.
- Rogalski A.** — Heterostructure infrared photodiodes, 3(2), 111-120.
- Rom M.A.** — See Zagoruiko Yu.A., Fedorenko O.A., Kovalenko N.O., Mateychenko P.V., 3(2), 165-169.
- Romanenko P.F.** — See Min'ko V.I., Indutnyy I.Z., Kudryavtsev A.A., 3(2), 251-253.
- Romanjuk B.** — Ultrasound effect on radiation damages in boron implanted silicon. — Krüger D., Melnik V., Popov V., Olikh Ya., Soroka V., Oberemok O.; 3(1), 15-18.
- Rud'ko G.Yu.** — See Masselink W.T., Kissel H., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Valakh M.Ya., Malyarchuk V., Zhuchenko Z.Ya., 3(2), 126-137.
- Ryzhikov V.D.** — Scintillators based on zinc selenide and tior for detection of charged particles. — Danshin E.A., Starzhinski N.G., Losseva E.A., Chernikov V.V., Litvinov L.A.; 3(2), 233-236.
- See Burachas S.F., Nagornaya L.L., Onishchenko G.M., Piven' L.A., Pirogov E.N., 3(2), 236-239.

- See Volkov V.G., Gavrilyuk V.P., Gal'chinetskii L.P., Grinyov B.V., Katrunov K.A., 3(2), 191-194.

S

- Sachenko A.V.** — Exciton-enhanced recombination in silicon at high concentrations of charge carriers. — Gorban A.P., Kostilyov V.P.; 3(1), 5-10.
- Excitonic effects in band-edge luminescence of semiconductors at room temperatures. — Kryuchenko Yu.V.; 3(2), 149-156.
- See Gorban' A.P., Kostilyov V.P., Prima N.A., 3(3), 322-329.
- Salo V.I.** — Effect of growth conditions on structure quality of KDP crystals. — Tkachenko V.F., Kolybayeva M.I., Pritula I.M.; 3(2), 203-206.
- Salo V.I.** — Rapidly grown KDP crystals; 3(2), 200-202.
- Savkina R.K.** — See Olikh Y.M., Vlasenko O.I., 3(3), 304-307.
- Schenderovskyy V.A.** — See Voznyy M.V., Gorley P.M., 3(3), 271-274.
- Selishchev P.A.** — Accumulation dynamics of oxygen clusters in silicon and formation of their nonhomogeneous distribution; 3(1), 19-21.
- Seliuta D.** — See Ašmontas S. Širmulis E.; 3(2), 138-143.
- Senchishin V.G.** — Manufacture and study of new polystyrene scintillators. — Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I.; 3(2), 223-226.
- Shaykevich I.A.** — Optical properties, form of granules and electronic parameters of binary Al/Cr composites. — Kolesnyk P.V.; 3(1), 77-81.
- Shchedrina L.V.** — See Blonsky I.V., Kosorotov V.F., Levash L.V., 3(2), 170-173.
- Shcherbak L.** - Structural changes in molten CdTe. - Feychuk P., Plevachuk Yu., Dong Ch., Sklyarchuk V.; 3(4), 456-459.
- Sheichenko D.M.** — Quantum-chemistry calculation of B_nN_n-rings ($n = 1-6$) and fulborenes, the fullerene-like molecules B_nN_n ($n = 12, 24, 60$). — Pokropivny A.V., Pokropivny V.V.; 3(4), 545-550.
- Sheinkman M.K.** — See Borkovskaya L.V., Dzhumaev B.R., Khomenkova L.Yu., Korsunskaya N.E., Markevich I.V.; 3(3), 282-286.
- Shepeliavyi P.** — See Park C.W., Lee J.-B., Do Y.R., Michailovs'ka K., Indutnyy I., Kudryavtsev A., 3(4), 496-499.
- Shirshov Yu.M.** — See Kruglenko I.V., Snopok B.A., Venger E.F., 3(4), 529-541.
- See Snopok B.A., Kostyukevych K.V., Beketov G.V., Zinio S.A., Venger E.F., Verevka S.V., 3(1), 59-68.
- See Goncharenko A.V., Snopok B.A., Venger E.F., Zavadskii S.N., 3(3), 389-393.
- Shnyr A.F.** — See Bonchik A.Yu., Dacko B.J., Demchuk V.I., Kiyak S.G., Palyvoda I.P., 3(3), 311-315.
- Shperun V.M.** — See Freik D.M., Galushchak M.O., Ivanishin I.M., Zapukhlyak R.I., Pyts M.V., 3(3), 287-290.
- Shpilinskaya L.N.** — The effect of oxygen-containing anions on luminescent properties of CsI. — Zaslavsky B.G., Kovaleva L.V., Vasetsky S.I., Kudin A.M., Mitichkin A.I., Charkina T.A.; 3(2), 178-180.
- Shpinar L.I.** — See Shwarts Yu.M., Kondrachuk A.V., Shwarts M.M., 3(3), 400-405.
- Shusterman S.** — See Dashevsky Z., Dariel M.P., 3(2), 181-184.
- Shwarts M.M.** — See Shwarts Yu.M., Kondrachuk A.V., Shpinar L.I., 3(3), 400-405.
- Shwarts Yu.M.** — Non-ohmic Mott conductivity and thermometric characteristics of heavily doped silicon structures. — Kondrachuk A.V., Shwarts M.M., Shpinar L.I.; 3(3), 400-405.
- Shydlovskij V.G.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova

- N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Mitsaj L.I., 3(2), 223-226.
- Sidel'nikova N.S.** — See Puzikov V.M., Dan'ko A.Ya., Adonkin G.T., Tkachenko V.F., Budnikov A.T., 3(2), 185-190.
- Simoen E.** — See Neimash V.B., Puzenko O.O., Kraitchinskii A.M., Kras'ko M.M., Putselyk S., Claeys C., 3(1), 11-14.
- Širmulis E.** — See Ašmontas S., Seliuta D.; 3(2), 138-143.
- Sizov F.F.** — Infrared detectors: outlook and means; 3(1), 52-58.
- Sklenař A.** — See Stronski A., Vlček M., 3(3), 394-399.
- Sklyarchuk V.** — See Shcherbak L., Feychuk P., Plevachuk Yu., Dong Ch., 3(4), 456-459.
- Slobodyanyuk A.** — See Valyukh S., Sorokin V., 3(2), 258-263.
- Slyno E.I.** — See Lashkarev G.V., Radchenko M.V., Vodopyanov V.N., Asotsky V.V., Kaminsky V.M., Beketov G.V., Rengevich E.V., 3(3), 295-299.
- Snopok B.A.** — Biochemical passivation of metal surfaces for sensor application: reactive annealing of polycrystalline gold films in hydrogen sulfide atmosphere. — Kostyukevych K.V., Beketov G.V., Zinio S.A., Shirshov Y.M., Venger E.F., Verevka S.V.; 3(1), 59-68.
- See Goncharenko A.V., Shirshov Yu.M., Venger E.F., Zavadskii S.N., 3(3), 389-393.
- See Kruglenko I.V., Shirshov Y.M., Venger E.F., 3(4), 529-541.
- Sokolov N.I.** — See Bazhenov M.Yu., Golod P.I., Grabovskyy V.V., Kurdyukov V.V., Tolmachev A.I., Il'chenko A.Ya., Zahaykevich G., 3(3), 423-425.
- Solomon A.M.** — See Hunda B.M., Puga P.P., Holovey V.M., 3(2), 227-232.
- Soloviev E.A.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova R.V., Lyapin V.G., Milenin V.V., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
- See Boltovets N.S., Goncharuk N.M., Krivutsa V.A., Chaika V.E., Konakova R.V., Milenin V.V., Tagaev M.B., Voitsikhovskiy D.I., 3(3), 353-358.
- Soloviev S.I.** — See Agueev O.A., Svetlichny A.M., 3(3), 379-382.
- Soloviev V.N.** — See Kiv A.E., Maximova T.I., 3(2), 157-160.
- Solsky I.** — See Zorenko Yu., Limarenko L., Konstankevych I., Pashkovsky M., Moroz Z., Grinev B., Nekrasov V., Borodenko Yu., 3(2), 207-212.
- Soroka V.** — See Romanjuk B., Krüger D., Melnik V., Popov V., Olikh Ya., Oberemok O., 3(1), 15-18.
- Sorokin V.** — See Valyukh S., Slobodyanyuk A., 3(2), 258-263.
- Soskin M.S.** — See Alexeyev C.N., Volyar A.V., 3(4), 500-513.
- Sosnin A.** — Image infrared converters based on ferroelectric-semiconductor thin-layer systems; 3(4), 489-495.
- Starzhinski N.G.** — See Ryzhikov V.D., Danshin E.A., Losseva E.A., Chernikov V.V., Litvinov L.A., 3(2), 233-236.
- Stronska O.J.** — See Karachevtseva L.A., Lytvynenko O.A., 3(1), 22-25.
- Stronski A.** — Photoinduced structural changes in $As_{100-x}S_x$ layers. — Vlček M., Sklenař A.; 3(3), 394-399.
- Svechnikov S.V.** — See Evtukh A.A., Kaganovich E.B., Litovchenko V.G., Litvin Yu.M., Fedin D.V., Manoilov E.G., 3(4), 474-478.
- Svetlichny A.M.** — See Agueev O.A., Soloviev S.I., 3(3), 379-382.
- See Agueev O.A., 3(3), 338-342.
- Syromiatnikov V.G.** — See Davidenko N.A., Kuvshinsky N.G., 3(1), 39-44.

T

- Tagaev M.B.** — See Boltovets N.S., Goncharuk N.M., Krivutsa V.A., Chaika V.E., Konakova R.V., Milenin V.V., Soloviev E.A., Voitsikhovskiy D.I., 3(3), 353-358.
- Tarasov G.G.** — See Masselink W.T., Kissel H., Mueller U., Walther C., Mazur Yu.I., Lisitsa M.P., Lavoric S.R., Zhuchenko Z.Ya., 3(2), 121-125.

- See Masselink W.T., Kissel H., Mueller U., Walther C., Mazur Yu.I., Rud'ko G.Yu., Valakh M.Ya., Malyarchuk V., Zhuchenko Z.Ya., 3(2), 126-137.
- Tetyorkin V.** — Paraelectric properties of PbTe doped with Ga. — Movchan S.; 3(3), 300-303.
- Titskaja V.D.** — See Senchishin V.G., Vasilchuk V.L., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Tkach V.M.** — See Prokopenko I.V., Kislovskii E.N., Olikhovskii S.I., Lytvyn P.M., Vladimirova T.P., 3(3), 275-281.
- Tkachenko V.F.** — See Puzikov V.M., Dan'ko A.Ya., Adonkin G.T., Sidel'nikova N.S., Budnikov A.T., 3(2), 185-190.
- See Salo V.I., Kolybayeva M.I., Pritula I.M., 3(2), 203-206.
- Tolmachev A.I.** — See Bazhenov M.Yu., Golod P.I., Grabovskyy V.V., Kurdyukov V.V., Il'chenko A.Ya., Sokolov N.I., Zahaykevich G., 3(3), 423-425.
- Tolmachev A.V.** — See Dubovik M.F., Grinyov B.V., Grin' L.A., Dolzhenkova E.F., Dobrotvorskaya M.V., 3(3), 420-422.
- See Grinyov B.V., Dubovik M.F., 3(3), 410-419.
- Trubitsyn Yu.V.** — Specificity of high-pure monocrystalline silicon production for various registering and converting devices. — Zverev S.V.; 3(2), 195-199.
- Tsvir A.V.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Belyaev A.E., Konakova R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
- Tyagulski I.P.** — See V.S. Lysenko, Y.V. Gomeniuk, I.N. Osiyuk, 3(3), 330-337.

V

- Vakulenko O.V.** — The influence of non-uniform deformation on photoelectric properties of crystalline silicon. — Kondratenko S.V.; 3(4), 453-455.
- Valakh M.Ya.** — See Masselink W.T., Kissel H., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Rud'ko G.Yu., Malyarchuk V., Zhuchenko Z.Ya., 3(2), 126-137.
- Valyukh S.** — Simulation of obliquely incident light propagation through a general twisted nematic liquid crystal cell by the Jones matrix technique. — Slobodyanyuk A., Sorokin V.; 3(2), 258-263.
- Vasetsky S.I.** — See Shpilinskaya L.N., Zaslavsky B.G., Kovaleva L.V., Kudin A.M., Mitichkin A.I., Charkina T.A., 3(2), 178-180.
- Vasilchuk V.L.** — See Senchishin V.G., Borisenko A.Yu., Lebedev V.N., Adadurov A.F., Khlapova N.P., Titskaja V.D., Koba V.S., Pelipyagina L.E., Miroshnichenko L.A., Leman V.E., Osadchenko V.N., Kluban N.A., Shydlovskij V.G., Mitsaj L.I., 3(2), 223-226.
- Venger E.F.** — See Baranskii P.I., Babich V.M., Dotsenko Yu.P., 3(4), 449-452.
- See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Voitsikhovskiy D.I., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
- See Demidenko A.A., Kochelap V.A., 3(4), 427-431.
- See Goncharenko A.V., Snopok B.A., Shirshov Yu.M., Zavadskii S.N., 3(3), 389-393.
- See Griban V.M., Melnichuk O.V., Ovander L.M., 3(2), 144-149.
- See Kruglenko I.V., Snopok B.A., Shirshov Y.M., 3(4), 529-541.
- See Snopok B.A., Kostyukevych K.V., Beketov G.V., Zinio S.A., Shirshov Y.M., Verevka S.V., 3(1), 59-68.
- Interface model of low temperature plasticity in high uniaxially strained monocrystalline semiconductors. — Kolomoets V.V., Machulin V.F.; 3(3), 291-294.
- Verevka S.V.** — See Snopok B.A., Kostyukevych K.V., Beketov G.V., Zinio S.A., Shirshov Y.M., Venger E.F., 3(1), 59-68.

- Vinnichenko K.L.** — See Kravets V.G., Prygun O.V., 3(4), 520-522.
- Virt I.S.** — Effect of thermal neutron irradiation on the electrophysical and photoelectric properties of $\text{Hg}_{0.8}\text{Cd}_{0.2}\text{Te}$ crystals. — Gorbunov V.V.; 3(1), 35-38.
- Vlček M.** — See Stronski A., Sklenář A., 3(3), 394-399.
- Vladimirova T.P.** — See Prokopenko I.V., Kislovskii E.N., Olikhovskii S.I., Tkach V.M., Lytvyn P.M., 3(3), 275-281.
- Vlasenko O.I.** — See Gnatyuk V.A., Gorodnychenko O.S., Mozol P.O.; 3(1), 26-30.
— See Olikh Y.M., Savkina R.K., 3(3), 304-307.
- Vodopiyanov V.N.** — See Lashkarev G.V., Radchenko M.V., Slynko E.I., Asotsky V.V., Kaminsky V.M., Beketov G.V., Rengevich E.V., 3(3), 295-299.
- Voitsikhovskiy D.I.** — See Boltovets N.S., Basanets V.V., Ivanov V.N., Krivutsa V.A., Tsvir A.V., Belyaev A.E., Konakova R.V., Lyapin V.G., Milenin V.V., Soloviev E.A., Venger E.F., Kholevchuk V.V., Mitin V.F., 3(3), 359-370.
— See Boltovets N.S., Goncharuk N.M., Krivutsa V.A., Chaika V.E., Konakova R.V., Milenin V.V., Soloviev E.A., Tagaev M.B., 3(3), 353-358.
- Volkov V.G.** — Small-grained detector of ionizing radiation based on ZnSe(Te). — Gavrilyuk V.P., Gal'chinetskii L.P., Grinyov B.V., Katrunov K.A., Ryzhikov V.D.; 3(2), 191-194.
- Volyar A.V.** — See Alexeyev C.N., Soskin M.S., 3(4), 500-513.
- Vorona I.** — New possibility of retrospective EPR dosimetry. — Ishchenko S., Okulov S., Petrenko T.T.; 3(2), 219-222.
- Voznyy M.V.** — Diffusion model of defect formation in silicon under light ion implantation. — Gorley P.M., Schenderovskyy V.A., 3(3), 271-274.
- Vyklyuk J.I.** — Calculation of absorption coefficients of $\text{InSb}_{1-x}\text{Bi}_x$ solid solutions. — Deibuk V.G., Rarenko I.M.; 3(2), 174-177.

W

- Walther C.** — See Masselink W.T., Kissel H., Mueller U., Mazur Yu.I., Tarasov G.G., Lisitsa M.P., Lavioric S.R., Zhuchenko Z.Ya., 3(2), 121-125.
— See Masselink W.T., Kissel H., Mueller U., Mazur Yu.I., Tarasov G.G., Rud'ko G.Yu., Valakh M.Ya., Malyarchuk V., Zhuchenko Z.Ya., 3(2), 126-137.

Z

- Zagoruiko Yu.A.** — Physical properties of ZnSe-MgSe, ZnSe-CdS solid solutions and possibilities of their application in IR engineering. — Fedorenko O.A., Kovalenko N.O., Rom M.A., Mateychenko P.V.; 3(2), 165-169.
— Strong thermostable interference coatings for IR optical elements. — Fedorenko O.A., Kovalenko N.O., Mateychenko P.V.; 3(2), 247-250.
— Thermostable power sensors for transmitted continuous radiation of CO- and CO₂- lasers. — Kovalenko N.O., Fedorenko O.A.; 3(4), 542-544.
- Zahaykevich G.** — See Bazhenov M.Yu., Golod P.I., Grabovskyy V.V., Kurdyukov V.V., Tolmachev A.I., Il'chenko A.Ya., Sokolov N.I., 3(3), 423-425.
- Zapukhlyak R.I.** — See Freik D.M., Galushchak M.O., Ivanishin I.M., Shperun V.M., Pyts M.V., 3(3), 287-290.
- Zaslavsky B.G.** — See Shpilinskaya L.N., Kovaleva L.V., Vasetsky S.I., Kudin A.M., Mitichkin A.I., Charkina T.A., 3(2), 178-180.
- Zavatskii S.N.** — See Goncharenko A.V., Snopok B.A., Shirshov Yu.M., Venger E.F., 3(3), 389-393.
- Zhovnir G.I.** — See Beketov G.V., Rashkovetskiy L.V., Rengevych O.V., 3(1), 45-51.
- Zhuchenko Z.Ya.** — See Masselink W.T., Kissel H., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Lisitsa M.P., Lavioric S.R., 3(2), 121-125.
— See Masselink W.T., Kissel H., Mueller U., Walther C., Mazur Yu.I., Tarasov G.G., Rud'ko G.Yu., Valakh M.Ya., Malyarchuk V., 3(2), 126-137.
- Zinio S.A.** — See Snopok B.A., Kostyukevych K.V., Beketov G.V., Shirshov Y.M., Venger E.F., Verevka S.V., 3(1), 59-68.
- Zorenko Yu.** — Application of scintillators based on single-crystalline $\text{Lu}_3\text{Al}_5\text{O}_{12}:\text{Ce}^{3+}$ films for radiation monitoring in biology and medicine. — Gorbenko V., Konstankevych I., Grinev B., Globus M., Batentschuk M.; 3(2), 213-218.
— Scintillation characteristics of the single crystalline CdWO_4 and $\text{Bi}_4\text{Ge}_3\text{O}_{12}$ compounds doped with mercury-like ions. — Limarenko L., Konstankevych I., Pashkovsky M., Moroz Z., Solsky I., Grinev B., Nekrasov V., Borodenko Yu.; 3(2), 207-212.
- Zvarev S.V.** — See Trubitsyn Yu.V., 3(2), 195-199.
- Żymierska D.** — Investigations of surface morphology and micro-relief of GaAs single crystals by complementary methods. — Auleytner J., Dmitruk N.; 3(4), 438-444.
- Żytkiewicz Z.** — See Klad'ko V.P., Datsenko L.I., Maksimenko Z.V., Lytvyn O.S., Prokopenko I.V., 3(3), 343-348.